



- (51) **International Patent Classification:**
H01L 27/115 (2006.01) *H01L 21/8247* (2006.01)
- (21) **International Application Number:**
PCT/US2010/054564
- (22) **International Filing Date:**
28 October 2010 (28.10.2010)
- (25) **Filing Language:** English
- (26) **Publication Language:** English
- (30) **Priority Data:**
12/610,922 2 November 2009 (02.11.2009) US
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- (81) **Designated States (unless otherwise indicated, for every kind of national protection available):** AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ,

CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

- (84) **Designated States (unless otherwise indicated, for every kind of regional protection available):** ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Declarations under Rule 4.17:

- as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii))

Published:

- with international search report (Art. 21(3))

- (88) **Date of publication of the international search report:**
29 September 2011

(54) **Title:** METHODS, STRUCTURES AND DEVICES FOR INCREASING MEMORY DENSITY

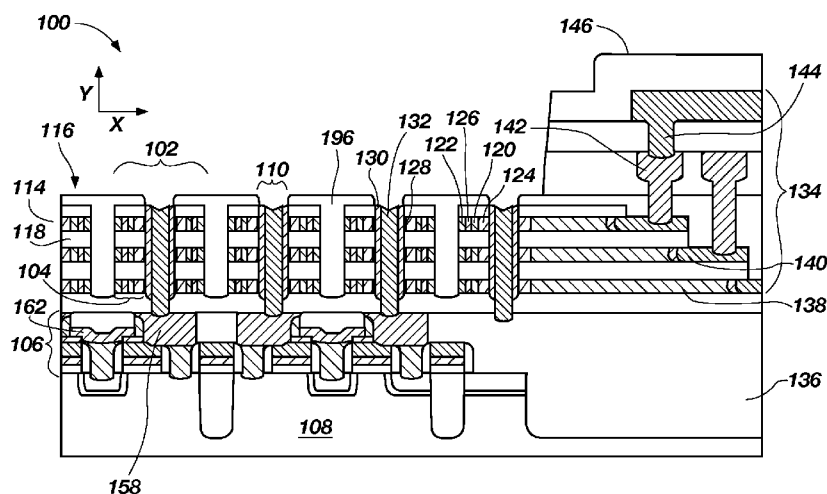


FIG. 1B

(57) **Abstract:** Non volatile memory devices comprising a memory string including a plurality of vertically superimposed diodes. Each of the diodes may be arranged at different locations along a length of the electrode and may be spaced apart from adjacent diodes by a dielectric material. The electrode may electrically couple the diodes of the memory strings to one another and to another memory device, such as, a MOSFET device. Methods of forming the non volatile memory devices as well as intermediate structures are also disclosed.